

In re Patent Application of:

COFFA ET AL.

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*B2*  
*and* a biasing device connected to said doped P/N junction for reverse biasing thereof.

Cancel Claim 29.

*B4*  
38. (Amended) A semiconductor laser device comprising:  
a semiconductor substrate;  
a doped P/N junction integrated with said semiconductor substrate, said P/N junction comprising a depletion layer and having a shape defining a waveguide, said depletion layer comprising at least one rare-earth material for providing a coherent light source; and  
a biasing device connected to said doped P/N junction for reverse biasing thereof.

39. (Amended) A semiconductor laser device according to Claim 38, wherein said at least one rare-earth material in the depletion layer of said doped P/N junction forms a base-collector region for a bipolar transistor.

Cancel Claim 40.

Claims 48-54 have been cancelled without prejudice to Applicants' right to file a divisional application directed to the subject matter thereof.